

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

- Epitaxial planar Silicon diode

FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

APPLICATIONS

- High Conductance Ultra Fast Diode
- For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

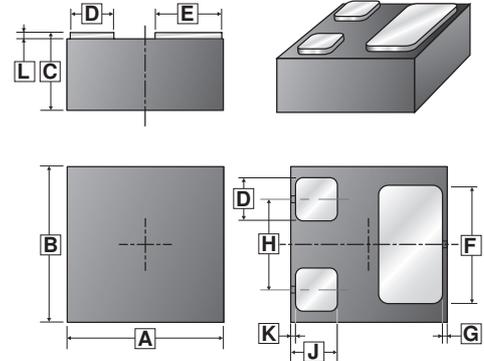
MARKING

T3

PACKAGE INFORMATION

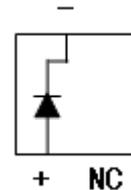
Package	MPQ	Leader Size
WBFBP-03D	5K	7 inch

WBFBP-03D



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.950	1.050	G	-	0.050
B	0.950	1.050	H	0.510	0.610
C	0.010	0.070	J	0.250	0.350
D	0.210	0.310	K	-	0.050
E	0.350	REF.	L	0.450	0.550
F	0.680	REF.			

TOP VIEW



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameters	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
Working Peak Reverse Voltage	V_{RWM}	200	V
DC Blocking Voltage	V_R	200	V
Forward Continuous Current	I_{FM}	400	mA
Average Rectified Output Current	I_o	200	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	$t=1.0\mu\text{s}$	2.5
		$t=1.0\text{s}$	0.5
Power Dissipation	P_D	100	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	1250	$^\circ\text{C} / \text{W}$
Operating Junction and Storage Temperature	$T_{J,STG}$	150, -65~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameters	Symbol	Min.	Max.	Unit	Test Conditions
Forward Voltage	V_{F1}	-	1	V	$I_F=100\text{mA}$
	V_{F2}	-	1.25	V	$I_F=200\text{mA}$
Reverse breakdown voltage	$V_{(BR)}$	200	-	V	$I_R=100\mu\text{A}$
Capacitance between terminals	C_T	-	5	pF	$V_R=0, f=1\text{MHz}$
Maximum DC Reverse Current at rated DC blocking voltage	I_R	-	0.1	μA	$V_R=200\text{V}$
Maximum Reverse Recovery Time	T_{RR}	-	50	nS	$I_F=I_R=30\text{mA}$

CHARACTERISTIC CURVES

